

#19/D

Attorney Docket No. 03692.P007XD

**PATENT**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

**RUMENNIK, et al.**

Serial No. 09/574,563

Filing Date: May 17, 2000

For: HIGH-VOLTAGE TRANSISTOR WITH  
MULTI-LAYER CONDUCTION REGION

Examiner: Hu, S.

Art Unit: 2811

RECEIVED  
SEP 17 2002  
FC 2800 MAIL ROOM

**Amendment and Response**

Hon. Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Sir:

This amendment and response is being submitted together with a Request for Continued Examination (RCE) following the Final Office Action mailed May 31, 2002, Applicants respectfully request the following amendments be entered and the

following remarks be considered:

01 FC:103 198.00 CH  
02 FC:102 84.00 CH

**In The Claims:**

1. (Unchanged) A high voltage field-effect transistor (HVFET) comprising:  
a substrate of a first conductivity type;  
a first region of a second conductivity type disposed within the substrate;  
a source diffusion region of the second conductivity type disposed in the substrate spaced-apart from the first region, a channel region being formed in the substrate between the source diffusion region and the first region;